

**BC869** TRANSISTOR (PNP)

## FEATURES

Power dissipation

 $P_{CM}$ : 500 mW ( $T_{amb}=25^{\circ}C$ )

Collector current

 $I_{CM}$ : -2 A

Collector-base voltage

 $V_{(BR)CBO}$ : -32 V

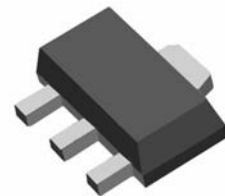
Operating and storage junction temperature range

 $T_J, T_{stg}$ :  $-65^{\circ}C$  to  $+150^{\circ}C$ **SOT-89**

1. BASE

2. COLLECTOR

3. EMITTER

**ELECTRICAL CHARACTERISTICS ( $T_{amb}=25^{\circ}C$  unless otherwise specified)**

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=-0.1mA, I_E=0$	-32		V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=-1mA, I_B=0$	-20		V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=-0.1mA, I_C=0$	-5		V
Collector cut-off current	$I_{CBO}$	$V_{CB}=-25V, I_E=0$		-0.1	$\mu A$
Emitter cut-off current	$I_{EBO}$	$V_{EB}=-5V, I_C=0$		-0.1	$\mu A$
DC current gain	$h_{FE(1)}$	$V_{CE}=-10V, I_C=-5mA$ $V_{CE}=-1V, I_C=-500mA$ $V_{CE}=-1V, I_C=-1A$	50 100 60	375	
	$h_{FE(2)}$	$V_{CE}=-1V, I_C=-500mA$	100 160	250 375	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=-1A, I_B=-100mA$		0.5	V
Transition frequency	$f_T$	$V_{CE}=-5V, I_C=-10mA$ $f=100MHz$	40		MHz

## DEVICE MARKING

BC869=CEC BC869-16=CGC BC869-25=CHC